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30V DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

Device	V _{(BR)DSS}	R _{DS(ON) max}	I _{D MAX} T _A = +25°C
N-Channel	30V	$20m\Omega$ @ $V_{GS} = 10V$	7.3A
N-Channel	30 V	$24m\Omega$ @ $V_{GS} = 4.5V$	6.7A

Description

This MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- DC Motor Control
- DC-AC Inverters

Features

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Mechanical Data

- Case: V-DFN3030-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Weight: 0.02 grams (Approximate)

D2 V-DFN3030-8 Pin 1 G1 D1 8 S1 7 2 D1 G1 3 S2 D2 4 D2 5 G2 **S1** Q1 N-Channel MOSFET Q2 N-Channel MOSFET Pin out Configuration Top View **Bottom View** (Bottom View) **Equivalent Circuit**

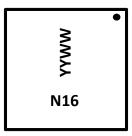
Ordering Information (Note 4)

Part Number	Case	Packaging
DMN3016LDN-7	V-DFN3030-8	3000/Tape & Reel
DMN3016LDN-13	V-DFN3030-8	10000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http"//www.diodes.com/products/packages.html.

Marking Information



N16 = Product Type Marking Code YYWW = Date Code Marking YY = Last Digit of Year (ex: 13 for 2013) WW = Week Code (01 ~ 53)



Maximum Ratings $(@T_A = +25^{\circ}C, \text{ unless otherwise specified.})$

Characteristic	Symbol	Value	Units		
Drain-Source Voltage	V_{DSS}	30	V		
Gate-Source Voltage			V_{GSS}	±20	V
		$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	7.3 5.8	А
Continuous Drain Current (Note 6) V _{GS} = 10V	t<10s	$T_A = +25$ °C $T_A = +70$ °C	I _D	9.2 7.3	А
Maximum Continuous Body Diode Forward Current	Is	2.5	Α		
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I _{DM}	45	Α
Avalanche Current (Note 7) L = 0.1mH			I _{AS}	22	Α
Avalanche Energy (Note 7) L = 0.1mH			Eas	24	mJ

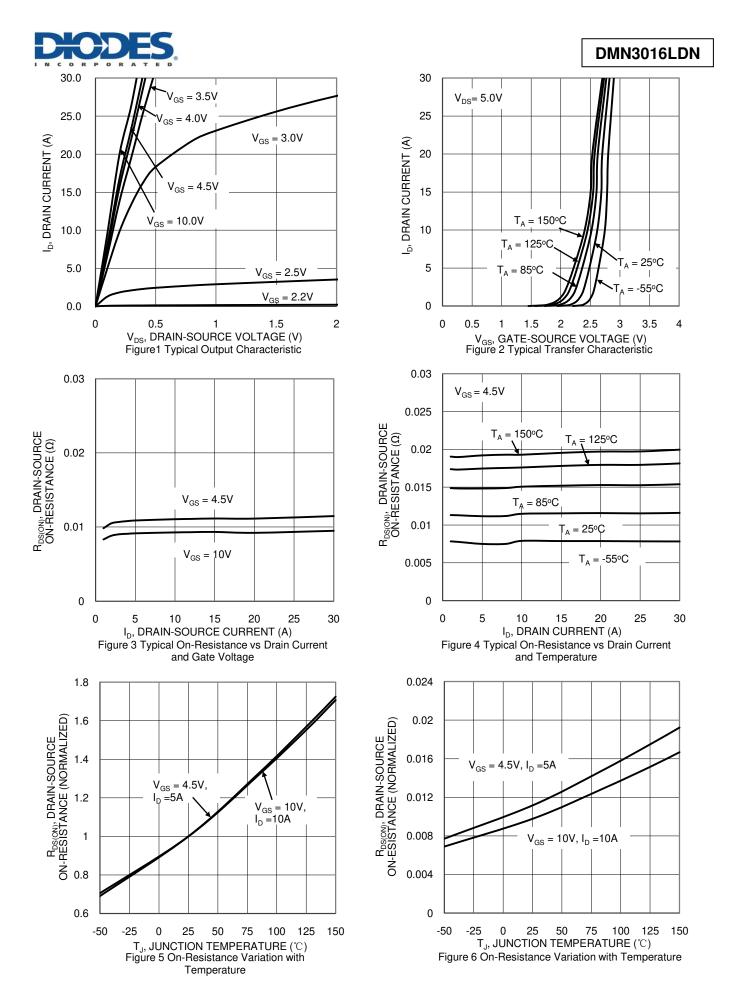
Thermal Characteristics

Characteristic		Symbol	Value	Units	
Total Power Dissipation (Note 5)	T _A = +25°C	P_{D}	1.1	W	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	D	119	°C/W	
Internal Resistance, Junction to Ambient (Note 5)	t<10s	$R_{\theta JA}$	75		
Total Power Dissipation (Note 6)	$T_A = +25^{\circ}C$	P_{D}	1.6	W	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	ם	78		
Thermal nesistance, Junction to Ambient (Note 6)	t<10s	R _{0JA}	49	°C/W	
Thermal Resistance, Junction to Case (Note 6)		$R_{ heta JC}$	13.5		
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C	

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV _{DSS}	30	-	-	V	$V_{GS} = 0V$, $I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	-	-	1	μΑ	$V_{DS} = 30V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	-	-	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V _{GS(TH)}	1.4	-	2.0	>	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
Static Drain-Source On-Resistance	В	-	-	20	mO	$V_{GS} = 10V, I_D = 11A$	
Static Drain-Source On-nesistance	R _{DS(ON)}	-	-	24	mΩ	$V_{GS} = 4.5V, I_D = 9A$	
Diode Forward Voltage	V _{SD}	-	0.70	1.0	V	$V_{GS} = 0V, I_{S} = 1A$	
DYNAMIC CHARACTERISTICS (Note 9)						•	
Input Capacitance	C _{iss}	-	1415	-		V _{DS} = 15V, V _{GS} = 0V, f = 1.0MHz	
Output Capacitance	Coss	-	119	-	pF		
Reverse Transfer Capacitance	Crss	-	82	-			
Gate Resistance	Rg	-	2.6	-	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Qg	-	11.3	-			
Total Gate Charge (V _{GS} = 10V)	Qg	-	25.1	-	nC	V _{DS} = 15V, I _D = 12A	
Gate-Source Charge	Q _{gs}	-	3.5	-	110	V _{DS} = 13V, I _D = 12A	
Gate-Drain Charge	Q_{gd}	-	3.6	-			
Turn-On Delay Time	t _{D(ON)}	-	4.8	-		$V_{DD} = 15V, V_{GS} = 10V,$ $R_L = 1.25\Omega, R_G = 3\Omega$	
Turn-On Rise Time	t _R	-	16.5	-	20		
Turn-Off Delay Time	t _{D(OFF)}	-	26.1	-	ns		
Turn-Off Fall Time	t _F	-	5.6	-			
Reverse Recovery Time	t _{RR}	-	12.3	-	ns	1 40A -11/-14 F00A/	
Reverse Recovery Charge	Q _{rr}	-	10.4	-	nC	I _F = 12A, di/dt = 500A/μs	

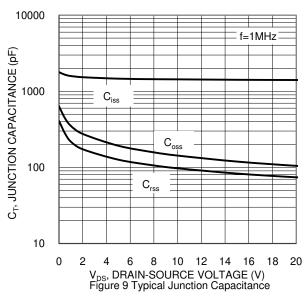
- 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1in. square copper plate.
 7. I_{AS} and E_{AS} rating are based on low frequency and duty cycles to keep $T_J = +25^{\circ}$ C.
- Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.

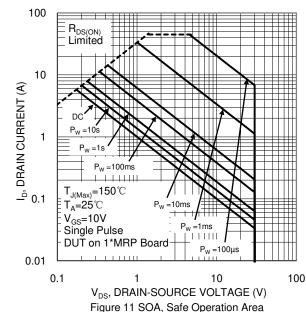




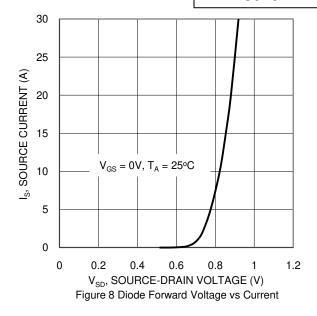
3 $V_{GS(TH)},$ GATE THESHOLD VOLTAGE (V) 2.5 2 $I_D = 1 \text{mA}$ 1.5 1 $I_D = 250 \mu A$ 0.5 0 -25 0 25 50 75 100 125 -50 T_J , JUNCTION TEMPERATURE ($^{\circ}$ C) Figure 7 Gate Theshold Variation vs Junction

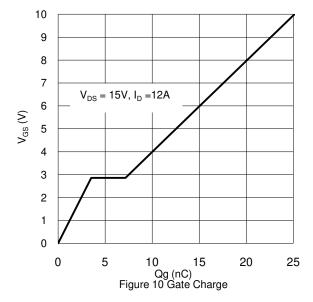
Temperature



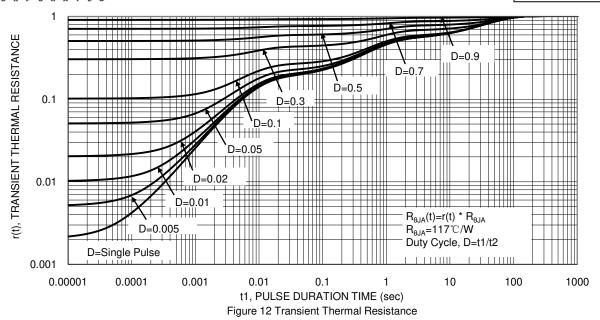


DMN3016LDN





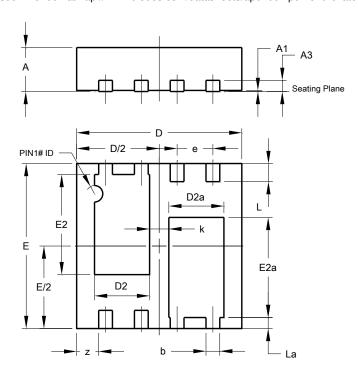






Package Outline Dimensions

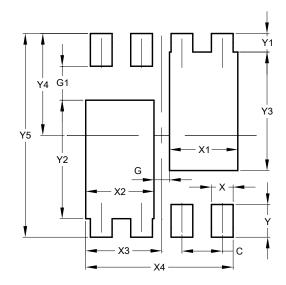
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



	V-DFN3030-8 (Type J)					
Dim	Min	Тур				
Α	0.77	0.83	0.80			
A1	0.00	0.05	0.02			
А3	0.	.203 BS	С			
b	0.20	0.30	0.25			
D	2.95	3.050	3.00			
D2	0.90	1.10	1.00			
D2a	0.90	1.10	1.00			
Е	2.95	3.050	3.00			
E2	1.72	1.92	1.82			
E2a	1.72	1.92	1.82			
е	0.65BSC					
L	0.27	0.38	0.33			
La	0.15	0.25	0.20			
k	0.35 TYP					
Z	0.40 BSC					
All Dimensions in mm						

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value			
Dillicipions	(in mm)			
С	0.650			
G	0.250			
G1	0.550			
X	0.350			
X1	1.100			
X2	1.100			
Х3	1.225			
X4	2.375			
Υ	0.530			
Y1	0.300			
Y2	1.920			
Y3	1.920			
Y4	1.650			
Y5	3.300			



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